

Self-excited current oscillations in a resonant tunneling diode described by a model based on the Caldeira-Leggett Hamiltonian

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Abstract. The quantum dissipative dynamics of a tunneling process through double barrier structures is investigated on the basis of a rigorous treatment. We employ a Caldeira-Leggett Hamiltonian with an effective potential calculated self-consistently, accounting for the electron distribution. With this Hamiltonian, we use the reduced hierarchy equations of motion in the Wigner space representation to study non-Markovian and non-perturbative thermal effects at finite temperature in a rigorous manner. We study the current-voltage relation of the resonant tunneling diode for several widths of the contact region, which consists of doped GaAs. Hysteresis and both single and double plateau-like behavior are observed in the negative differential resistance (NDR) region. While all of the current oscillations decay in time in the NDR region in the case of a strong system-bath coupling, there exist non-transient oscillations in some parts of the plateau in the NDR region in the case of weak coupling. We find that the effective potential in the oscillating case possesses a basin-like form on the emitter side (emitter basin) and that the current oscillation results from tunneling between the emitter basin and the quantum well in the barriers. We find two distinct types of current oscillations, with large and small oscillation amplitudes, respectively. The results of eigenstates analysis indicate that the first type is caused by a transition between ground tunneling states and adjacent excited states in the emitter basin, while the second type is caused by a transition between intermediate tunneling states and higher states. These two types of oscillation also appear differently in the Wigner space, with one exhibiting tornado-like motion and the other exhibiting a two piston engine-like motion.

1. Introduction

Quantum coherence and its destruction by coupling to a dissipative environment play an important role in the transport phenomena of a particle moving in a potential. Well known examples include electron transfer in molecular and biological systems [1, 2, 3, 4], many chemical reactions [5, 6, 7, 8], SQUID rings [9, 10], quantum ratchets [11, 12], nonlinear optical processes [13, 14], and tunneling processes in device systems [15, 16]. Such systems are commonly modeled as one-dimensional or two-dimensional potential systems coupled to heat bath degrees of freedom, which drive the systems toward the thermal equilibrium state. The heat bath degrees of freedom are then reduced using such methods as the projection operator method or the path integral method, for example. Many equations of motion have been derived for the purpose of understanding the quantum aspects of dissipative dynamics [17, 18, 19, 20, 21, 22, 23, 24, 25]. Because a complete picture of quantum dissipative dynamics must treat phenomena that can only be described in real time, a great deal of effort has been dedicated to the problem of numerically integrating these equations of motion in real time [22, 23, 24, 25, 26, 27, 28, 29]. Although these equations are analogous to the classical kinetic equations, which have proved to be useful for classical transport problems, such equations cannot be derived in a quantum mechanical framework without significant approximations and/or assumptions. For example, the quantum Boltzmann equation is based on the assumption that the effects of collisions between electrons can be described by the rates determined from Fermi's golden rule, and hence it is regarded as a semi-classical equation [17, 18, 19]. Similarly, the quantum Fokker-Planck equation can be derived from the Caldeira-Leggett Hamiltonian under a Markovian approximation, but in order for this to be possible, the heat bath must be at a sufficiently high temperature, in which case most of the important quantum dynamical effects play a minor role [20, 21]. Thus, treatments of the above kinds cannot be used to construct fully quantum mechanical descriptions of broad validity. In this paper, we present a rigorous quantum mechanical treatment that solves this problem. This treatment employs the reduced hierarchy equations of motion (HEOM), and it can be used in application to systems for which fully quantum mechanical description is necessary. In particular, the reduced HEOM approach can be used to numerically treat non-Markovian system-bath coupling in a non-perturbative manner. Here, we apply this approach to study the dynamics of a resonant tunneling diode (RTD) described by the Caldeira-Leggett Hamiltonian [30, 31, 32, 33, 34, 35, 36, 37, 38, 39, 40].

The RTD system that we consider is modeled by a double barrier structure with an electrostatic potential representing a region consisting of an undoped layer positioned between two doped layers. A second potential, arising from the charge distribution, is determined self-consistently [15, 16]. Due to quantum effects, RTD systems exhibit novel negative differential resistance (NDR) in the current-voltage (I-V) relation [41]. Moreover, current oscillations [42], plateau-like behavior and hysteresis of the I-V curve have been observed in the NDR region [43]. Goldman et al. attributed these phenomena

to intrinsic charge bistability. However, Sollner claimed that they result merely from resonance with the external circuit [44]. Resonant tunneling diodes are presently the highest-frequency active semiconductor devices in existence [45, 46, 47, 48, 49]. Although oscillation frequencies above 1 THz have recently been realized [50, 51, 52], the causes of such phenomena have not yet been definitely identified. In these phenomena, dissipation and fluctuations arise from interaction with the heat bath, which plays an essential role as the origin of resistance.

Frensley et al. discovered NDR in the I-V curve through a numerical computation treating a quantum Liouville equation in the Wigner representation that ignored phonon-scattering processes [53, 54, 55, 56, 57, 58]. Kluksdahl et al. incorporated dissipative and self-consistent effects, employing the Poisson-Boltzmann equation by adopting a relaxation time approximation, and succeeded in modeling the experimentally observed hysteresis behavior of the I-V curve [60]. Jensen and Buot developed a numerical scheme to treat systems of the same kind and found evidence that the current oscillation and plateau-like behavior arise from intrinsic bistability [61, 62]. However, because there exists no well-established methodology that can be applied rigorously to this type of model and includes the effect of dissipation, which is the origin of Joule heat, its application in describing the dynamics of systems under such conditions has been quite limited.

In a previous study [63], we demonstrated through consideration of a RTD that with the HEOM approach, the effects of non-Markovian thermal fluctuations and dissipation at finite temperature on quantum transport can be investigated rigorously. We found that while most of the current oscillations decay in time in the NDR region, there exists persistent oscillation in a plateau of the NDR region. In this paper, we explore the cause of current oscillation by considering several widths of the doped contact regions and two different cases for the strength of the system-bath coupling. The value of the noise correlation time is also chosen to be twice shorter than the previous study.

This paper is organized as follows. In Sec. 2, we introduce the reduced hierarchy equations of motion applicable to the resonant tunneling problem. We then present the computational details for the numerical simulations in Sec. 3. Numerical results for the I-V curves and current oscillations are presented in Secs. 4. Section 5 is devoted to concluding remarks.

2. Formulation

We consider the following Caldeira-Leggett Hamiltonian [6], which describes the dynamics of an electron subjected to a thermal environment:

$$\hat{H} = \frac{\hat{p}^2}{2m} + U(\hat{q}; t) + \sum_j \left[\frac{\hat{p}_j^2}{2m_j} + \frac{m_j \omega_j^2}{2} \left(\hat{x}_j - \frac{a_j V(\hat{q})}{m_j \omega_j} \right)^2 \right]. \quad (1)$$

Here, m , $\hat{p}$, and $\hat{q}$ are the mass, momentum and position variables of the electron, and m_j , $\hat{p}_j$, $\hat{x}_j$ and ω_j are the mass, momentum, position and frequency variables of the j th

phonon oscillator mode. In equation (1), the electron-phonon interaction is given by

$$\hat{H}_I = -V(\hat{q}) \sum_j a_j \hat{x}_j. \quad (2)$$

Here, $V(\hat{q})$ is any function of $\hat{q}$ and the quantities a_j are coefficients that depend on the nature of the electron-phonon coupling.

The heat bath can be characterized by the spectral distribution function, defined by

$$J(\omega) \equiv \sum_j \frac{a_j^2}{2m_j\omega_j} \delta(\omega - \omega_j), \quad (3)$$

and the inverse temperature, $\beta \equiv 1/k_B T$, where k_B is the Boltzman constant. We assume the Drude distribution, given by

$$J(\omega) = \frac{m\zeta}{\pi} \frac{\gamma^2 \omega}{\gamma^2 + \omega^2}, \quad (4)$$

where the constant γ represents the width of the spectral distribution of the collective phonon modes and is the reciprocal of the correlation time of the noise induced by phonons. The parameter ζ is related to the electron-phonon coupling strength. For the collective heat bath coordinate $\hat{X} = \sum_j a_j \hat{x}_j$, the canonical and symmetrized correlation functions, respectively defined by $\Psi(t) \equiv \beta \langle \hat{X}; \hat{X}(t) \rangle_B$ and $C(t) \equiv \frac{1}{2} \langle \hat{X}(t) \hat{X}(0) + \hat{X}(0) \hat{X}(t) \rangle_B$, where $\hat{X}(t)$ is the Heisenberg representation of $\hat{X}$, and $\langle \cdots \rangle_B$ represents the thermal average over the bath modes, are given by [31, 30]

$$\Psi(t) = -\frac{m\zeta\gamma}{\hbar} e^{-\gamma|t|}, \quad (5)$$

and

$$C(t) = c_0 e^{-\gamma|t|} + \sum_{k=1}^{\infty} c_k e^{-\nu_k|t|}. \quad (6)$$

Here, $\nu_k \equiv 2\pi k/\beta\hbar$ are the Matsubara frequencies, and we have

$$c_0 = \frac{\hbar m \zeta \gamma^2}{2} \left[\frac{2}{\beta \hbar \gamma} + \sum_{k=1}^{\infty} \frac{4\beta \hbar \gamma}{(\beta \hbar \gamma)^2 - (2\pi k)^2} \right], \quad (7)$$

and

$$c_k = -\frac{\hbar m \zeta \gamma^2}{2} \frac{8\pi k}{(\beta \hbar \gamma)^2 - (2\pi k)^2}. \quad (8)$$

The function $C(t)$ is analogous to the classical correlation function of $X(t)$ and corresponds to the correlation function of the bath-induced noise, whereas $\Psi(t)$ corresponds to dissipation. The noise $C(t)$ is related to $\Psi(t)$ through the quantum version of the fluctuation-dissipation theorem, $C[\omega] = \hbar\omega \coth(\beta\hbar\omega/2)/2\Psi[\omega]$, which insures that the system exists in the thermal equilibrium state for finite temperatures [64]. Note that in the high temperature limit, $\beta\hbar\gamma \ll 1$, the noise correlation function reduces to $C(t) \propto e^{-\gamma|t|}$. This indicates that the heat bath oscillators interact with the system in the form of Gaussian-Markovian noise.

To derive the equation of motion for the electron, we use the reduced density operator of the system by taking the trace over the heat bath degrees of freedom:

$$\hat{\rho}(t) = \text{Tr}_B \hat{\rho}_{\text{tot}}(t). \quad (9)$$

In the path integral representation, the reduced density matrix elements are written

$$\begin{aligned} \rho(q, q'; t) &= \int D[q(\tau)] \int D[q'(\tau)] \int dq_i \int dq'_i \rho(q_i, q'_i) \rho_{CS}(q, q', t; q_i, q'_i) \\ &\times e^{\frac{i}{\hbar} S_A[q; t]} F[q, q'; t] e^{-\frac{i}{\hbar} S_A[q'; t]}, \end{aligned} \quad (10)$$

where $S_A[q; t]$ is the action for the system's Hamiltonian $\hat{H}_A = p^2/2m + U(q; t)$,

$$S_A[q; t] \equiv \int_{t_i}^t d\tau \left[\frac{1}{2} m \dot{q}^2(\tau) - U(q(\tau); \tau) \right], \quad (11)$$

$\rho(q_i, q'_i)$ is the initial state of the system at time t_i , $F[q, q'; t]$ is the influence functional [65], and $\rho_{CS}(q, q', t; q_i, q'_i)$ is the initial correlation function between the system and the heat bath [66]. The functional integrals for $q(\tau)$ and $q'(\tau)$ are carried out from $q(t_i) = q_i$ to $q(t) = q$ and from $q'(t_i) = q'_i$ to $q'(t) = q'$, respectively. In our approach, we can set $\rho_{CS}(q, q', t; q_i, q'_i) = 1$ and regard $\rho(q_i, q'_i)$ as the initial condition without loss of generality. This is due to the fact that the effects of the initial correlation can be taken into account through implementation of a hierarchy of initial conditions that can be evaluated numerically. The influence functional for the inverse temperature β is given by [65, 66]

$$\begin{aligned} F[q, q'; t] &= \exp \left\{ \left(-\frac{i}{\hbar} \right)^2 \int_{t_i}^t d\tau V^\times(q, q'; \tau) \right. \\ &\times \left[\frac{\partial}{-\partial \tau} \int_{t_i}^\tau d\tau' \frac{i\hbar}{2} \Psi(\tau - \tau') V^\circ(q, q'; \tau') + \int_{t_i}^\tau d\tau' C(\tau - \tau') V^\times(q, q'; \tau') \right] \Bigg\}, \end{aligned} \quad (12)$$

where $V^\times(q, q'; \tau) \equiv V(q(\tau)) - V(q'(\tau))$ and $V^\circ(q, q'; \tau) \equiv V(q(\tau)) + V(q'(\tau))$. If we choose K so as to satisfy $\nu_K = 2\pi K/(\beta\hbar) \gg \omega_c$, where ω_c is the characteristic frequency of the system, the factor $e^{-\nu_k|t|}$ in equation (6) can be replaced with Dirac's delta function, using the approximation $\nu_k e^{-\nu_k|t|} \simeq \delta(t)$ (for $k \geq K+1$). Therefore, $C(t)$ can be expressed as

$$C(t) = c_0 e^{-\gamma|t|} + \sum_{k=1}^K c_k e^{-\nu_k|t|} + \delta(t) \sum_{k=K+1}^{\infty} \frac{c_k}{\nu_k}. \quad (13)$$

The reduced hierarchy equations of motion (HEOM) can be obtained by considering the time derivative of the reduced density matrix with the kernel given in equations (5) and (13). The HEOM have been used to study chemical reactions [32, 33, 67, 68], linear and nonlinear spectroscopy [34, 35, 36, 37, 38, 39, 40, 69, 70, 71], exciton transfer [72, 73, 74, 75, 76, 77], electron transfer [78, 79, 80, 81], quantum dots [82, 83], and quantum information [84, 85, 86]. A variety of numerical techniques have been developed for the HEOM approach in order to accelerate numerical calculations [87, 88, 89, 90, 91, 92].

The HEOM are ideal for studying quantum transport systems, in conjunction with the Wigner representation, characterized by the Wigner distribution function,

$$W(p, q; t) \equiv \int_{-\infty}^{\infty} dr e^{-\frac{ipr}{\hbar}} \rho \left(q + \frac{r}{2}, q - \frac{r}{2}; t \right), \quad (14)$$

because they allow us to treat continuous systems utilizing open boundary conditions and periodic boundary conditions [55, 56]. The Wigner distribution function is the quantum analogue of the classical distribution function in the phase space [53, 54, 55, 56, 57, 58, 59]. Its classical limit can be computed readily. This is helpful, because knowing the classical limit allows us to identify the purely quantum mechanical effects [32, 33, 40].

Although we can handle any form of $V(q)$ [35, 36, 37, 38, 39, 40], here we consider the liner-liner system bath coupling case defined by $V(q) = q$. In the Wigner representation, the equations of motion are expressed in hierarchical form as follows [30, 40]:

$$\begin{aligned} \frac{\partial}{\partial t} W_{j_1, \dots, j_K}^{(n)}(t) = & - \left[\hat{L}_{\text{qm}} + \hat{\Xi}' + n\gamma + \sum_{k=1}^K j_k \nu_k \right] W_{j_1, \dots, j_K}^{(n)}(t) \\ & + \hat{\Phi} \left[W_{j_1, \dots, j_K}^{(n+1)}(t) + \sum_{k=1}^K W_{j_1, \dots, (j_k+1), \dots, j_K}^{(n)}(t) \right] \\ & + n\gamma \hat{\Theta}_0 W_{j_1, \dots, j_K}^{(n-1)}(t) + \sum_{k=1}^K j_k \nu_k \hat{\Theta}_k W_{j_1, \dots, (j_k+1), \dots, j_K}^{(n)}(t) \end{aligned} \quad (15)$$

for non-negative integers $n, j_1, \dots, j_K$, where we have chosen K such that $\nu_k \gg \omega_c$. In equation (15), $-\hat{L}_{\text{qm}}$ is the quantum Liouvillian in the Wigner representation, given by

$$-\hat{L}_{\text{qm}} W(p, q) \equiv -\frac{p}{m} \frac{\partial}{\partial q} W(p, q) - \frac{1}{\hbar} \int_{-\infty}^{\infty} \frac{dp'}{2\pi\hbar} U_{\text{W}}(p - p', q; t) W(p', q) \quad (16)$$

with

$$U_{\text{W}}(p, q; t) \equiv 2 \int_0^{\infty} dr \sin \left(\frac{pr}{\hbar} \right) \left[U \left(q + \frac{r}{2}; t \right) - U \left(q - \frac{r}{2}; t \right) \right]. \quad (17)$$

The other operators appearing in equation (15) are the bath-induced relaxation operators, defined as

$$\hat{\Phi} \equiv \frac{\partial}{\partial p}, \quad (18)$$

$$\hat{\Theta}_0 \equiv \zeta \left[p + \frac{m\hbar\gamma}{2} \cot \left(\frac{\beta\hbar\gamma}{2} \right) \frac{\partial}{\partial p} \right], \quad (19)$$

$$\hat{\Theta}_k \equiv \frac{m\zeta}{\beta} c_k, \quad (20)$$

and

$$\hat{\Xi}' \equiv -\frac{m\zeta}{\beta} \left[1 - \frac{\beta\hbar\gamma}{2} \cot \left(\frac{\beta\hbar\gamma}{2} \right) - \sum_{k=1}^K c_k \right]. \quad (21)$$

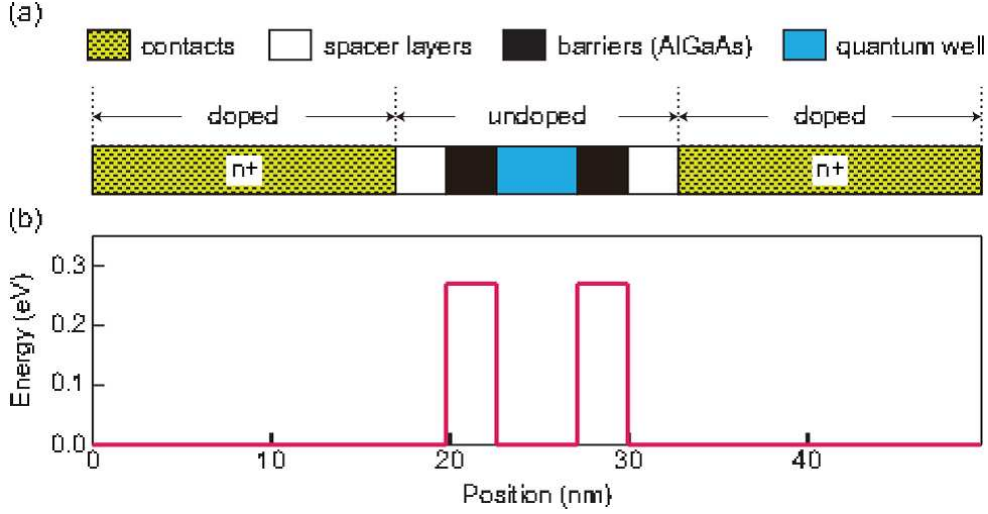


Figure 1. (a) The structure of the RTD. The well consists of undoped GaAs (4.520 nm), the barriers consist of undoped AlGaAs (2.825 nm), the spacer layers consist of undoped GaAs (2.825 nm), and the contact regions consist of doped GaAs (with a doping concentration of $2 \times 10^{18} \text{ cm}^{-3}$). In order to elucidate the dependence of the current on the width of the contact regions, we carried out computations for three values of this widths: (i) 16.950 nm; (ii) 33.900 nm; (iii) 42.375 nm. This figure depicts the case of 16.950 nm. (b) The structure of the conduction band edge. The height of the potential barriers is 0.27 eV.

In the case that the quantity $N \equiv n + \sum_{k=1}^K j_k$ satisfies the relation $N \gg \omega_c / \min(\gamma, 1/\beta\hbar)$, this finite hierarchy can be truncated with negligible error by the terminator [40]

$$\frac{\partial}{\partial t} W_{j_1, \dots, j_K}^{(n)}(t) = -(\hat{L}_{\text{qm}} + \hat{\Xi}') W_{j_1, \dots, j_K}^{(n)}(t). \quad (22)$$

Note that only $W_{0, \dots, 0}^{(0)}(p, q; t) \equiv W(p, q; t)$ has physical meaning, and the other elements $W_{j_1, \dots, j_K}^{(n)}(p, q; t)$ with $(n; j_1, \dots, j_K) \neq (0; 0, \dots, 0)$ are auxiliary operators introduced to avoid the explicit treatment of the inherent memory effects that arise in the time evolution of the reduced density matrix. In the classical limit, $\hbar \rightarrow 0$, the Wigner distribution function corresponds to the classical distribution function. If the noise correlation is very short ($\gamma \rightarrow \infty$) and the temperature is high (i.e., the noise is white), the quantum Fokker-Planck equation can be derived in a form similar to that of Kramers equation [20, 21]. In the present case, however, we cannot employ the white noise approximation, because quantum effects play a dominant role in the low temperature regime ($\beta\hbar\omega_c \gg 1$). Although the original quantum Fokker-Planck equation, derived by Caldeira and Leggett, is valid only for sufficiently high temperatures ($\beta\hbar\omega_c \ll 1$) [20], our formulation is valid for arbitrary temperature, and it can be applied without approximation.

In equation (17), $U(\hat{q}; t)$ is the effective potential for the electron, which can be

written [60, 61, 62]

$$U(\hat{q}; t) = U_{static}(\hat{q}) + U_{self}(\hat{q}; t), \quad (23)$$

where $U_{static}(\hat{q})$ and $U_{self}(\hat{q}; t)$ are the static and self-consistent parts, respectively. As the static potential, we employ the double-barrier structure depicted in figure 1. The self-consistent part, $U_{self}(q; t) = -e\phi(q; t)$, is calculated from the electron distribution at each time step in the integration of equation (15) using the Poisson equation

$$-\frac{\partial}{\partial q} [\epsilon\phi(q; t)] = e [n^+(q) - P(q, t)], \quad (24)$$

where ϵ is the dielectric constant, $n^+(q)$ is the doping density and $P(q; t) = \int_{-\infty}^{\infty} dp / (2\pi\hbar) W_{0,\dots,0}^{(0)}(p, q; t)$ is the electron density calculated from the Wigner distribution. Coupling the HEOM to the Poisson equation, we obtain a fully self-consistent model of quantum electron transport. This allows us to examine charge redistribution effects.

3. Computational details

The equations of motion given in (15) were numerically evaluated using finite mesh representations of the Wigner distribution functions. The spatial derivative of the kinetic term in the Liouville operator, $-(p/m)\partial W(p, q)/\partial q$, was approximated by using a third-order left-handed or right-handed difference scheme, depending on the sign of the momentum, given by

$$\begin{aligned} \frac{\partial W(p_k, q_j)}{\partial q} = \frac{1}{6\Delta q} & (W(p_k, q_{j+1}) + 3W(p_k, q_j) \\ & - 6W(p_k, q_{j-1}) + W(p_k, q_{j-2})) \end{aligned} \quad (25)$$

for $p_k > 0$, and

$$\begin{aligned} \frac{\partial W(p_k, q_j)}{\partial q} = \frac{1}{6\Delta q} & (-W(p_k, q_{j+2}) + 6W(p_k, q_{j+1}) \\ & - 3W(p_k, q_j) + 2W(p_k, q_{j-1})) \end{aligned} \quad (26)$$

for $p_k < 0$, in order to facilitate implementation of the inflow and outflow boundary conditions [53, 54, 55]. Note that the first-order difference scheme is not sufficiently accurate for the present problem, because this scheme introduces artificial viscosity for the wavepacket dynamics, which damps the self-excited current oscillations.

The inflow boundary conditions were set by stipulating that $W_{j_1, \dots, j_k}^{(n)}(p < 0, q = L)$ and $W_{j_1, \dots, j_k}^{(n)}(p > 0, q = 0)$ are given by the equilibrium distribution of a free particle calculated from the HEOM with periodic boundary conditions. Due to fluctuations and dissipation, the flow of a wavepacket reaches a steady state even when there exists a non-zero bias voltage. The validity of the boundary conditions was verified by considering several system sizes.

Other derivatives with respect to p were approximated using the fourth-order centered difference scheme given by

$$\frac{\partial W(p_k, q_j)}{\partial p} = \frac{1}{12\Delta p} (-W(p_{k+2}, q_j) + 8W(p_{k+1}, q_j) - 8W(p_{k-1}, q_j) + W(p_{k-2}, q_j)), \quad (27)$$

and

$$\frac{\partial^2 W(p_k, q_j)}{\partial p^2} = \frac{1}{12\Delta p^2} (-W(p_{k+2}, q_j) + 16W(p_{k+1}, q_j) - 30W(p_k, q_j) + 16W(p_{k-1}, q_j) - W(p_{k-2}, q_j)). \quad (28)$$

The mesh size for the position, Δq , and momentum, Δp , are respectively 0.2825 nm and 3.540 nm^{-1} .

We set the parameters used in the HEOM as $\gamma = 24.2 \text{ THz}$ ($\gamma^{-1} = 4.13 \text{ fs}$), $\zeta = 72.5 \text{ GHz}$ ($\zeta^{-1} = 13.8 \text{ ps}$), and $T = 300 \text{ K}$ in order to create conditions close to those used in previous theoretical studies. In Appendix B, we also report the results of calculations for the strong coupling case, with $\zeta = 120.8 \text{ GHz}$ ($\zeta^{-1} = 8.28 \text{ ps}$), to elucidate the role of dissipation. The depth of the hierarchy and the number of Matsubara frequencies were chosen as $N \in \{2-6\}$ and $K \in \{1-3\}$, respectively. The effective mass of the electron was assumed to be constant across the device and equal to $0.067m_0$, where m_0 is the electron mass in vacuum. The dielectric constant in equation (24) was set as $\epsilon = 12.85$.

As the static double-barrier potential, which models the hetero-structure of GaAs sandwiched between two thin AlGaAs layers, we set the widths of quantum well (undoped GaAs), barrier (undoped AlGaAs), and spacer layer (undoped GaAs) to be 4.520 nm, 2.825 nm, and 2.825 nm, respectively. The height of the potential barriers was 0.27 eV. The conduction band edge consists of a single quantum well bounded by tunneling barriers (figure 1 (b)). The widths of the contact regions (the yellow parts in figure 1(a), where GaAs is doped with a concentration of $2 \times 10^{18} \text{ cm}^{-3}$) were chosen as 16.950 nm, 33.900 nm, and 42.375 nm.

In a previous study [63], we chose a smaller value of γ , $\gamma = 12.1 \text{ THz}$ ($\gamma^{-1} = 8.26 \text{ fs}$), and fixed the width of the contact region as 42.375 nm. In that case, we found hysteresis, double plateau-like behavior, and self-excited current oscillation in the negative differential resistance (NDR) region of the current-voltage curve. We found that while most of the current oscillations decay in time in the NDR region, there exists a non-transient oscillation characterized by a tornado-like rotation in the Wigner space in the upper plateau of the NDR region. In this paper, we explore the cause of such current oscillations by considering several values of the width of the contact regions in cases of both weak and strong coupling, characterized by different values of ζ .

4. Results

We determined the characteristics of the current-voltage (I-V) according to the following procedure. First, we integrated equation (15) at zero bias voltage without the self-consistent part of the effective potential under the inflow boundary conditions specified

above. When we obtained the *temporal* steady state, the obtained distribution was then used as the initial distribution for the self-consistent calculation, and we then integrated equation (15) again, with the effective potential $U(\hat{q}; t)$ evaluated iteratively using the Poisson equation given in (24). Under this procedure, when the distributions reached the *genuine* steady state $W_{j_1, \dots, j_K}^{(n)}(p, q; t \rightarrow \infty)$, the current was calculated by $I(t) = \int dp p W_{0, \dots, 0}(p, q; t) / 2\pi m^2 \hbar$ and then the *genuine* state was used as the initial distributions for the next bias step. Note that if we were to omit the first step of the calculation, which does not contain the self-consistency procedure, there would be cases in which the distribution does not reach the steady state, in particular when the contact regions are wide. Following the above steps, we increased the bias from 0.000V to 0.500V, and then decreased it to 0.000V with bias steps of 0.01 V in the normal region and 0.002 V in the negative differential resistance (NDR) region. At each step, we integrated the equation of motion until the system reached the steady state distribution. However, in some cases, in the NDR region, current oscillation arose, and a steady state was thus not realized. In such cases, the value of current was evaluated as a time average between 30 ps to 40 ps.

In figure 2, we present (a) current-voltage (I-V) relations and (b) the time evolution of the self-excited current oscillation in the weak coupling case ($\zeta = 72.5$ GHz) for three values of the width of the contact regions (the yellow parts in figure 1(a)). In these plots, the sizes of the contact regions are (i) 16.950 nm, (ii) 33.900 nm, and (iii) 42.375 nm, respectively, with a fixed doping concentration of GaAs. These graphs reveal NDR behavior, hysteresis, and plateaus in the I-V curve. Moreover, self-excited current oscillation appears in some regions of the plateau. While Jensen and Buot observed only a single plateau similar to that in figure 2 (i-a) with current oscillation [61], our results in figure 2(ii-a) and 2(iii-a) exhibit a double plateau structure. In the case of a single plateau structure, the width of the plateau is large for a narrow contact region, while in the case of a double plateau structure, the width is small for a wide contact region. For the sake of comparison, the I-V curves obtained in the strong coupling case ($\zeta = 120.8$ GHz) are presented in Appendix B. In that case, NDR behavior, hysteresis, and a single plateau in the I-V curve are observed, but steady current oscillation does not appear, even in the plateau.

As in the case considered in the previous paper [63], we find that most of the current oscillations decay in time in the NDR region, but there also exist non-decaying oscillations in some regions of the plateau, as seen in figures 2 (i-b) - (iii-b). The Fourier components of each persistent oscillation are plotted in figures 3 (i-a) - (iii'-a). We can classify these oscillations into two types, according to the current amplitude. The first type is observed in the single plateau (figure 2(i)) and the lower part of the double-plateau (figure 2(iii)) with large amplitude (red). The plateau in this case is located in the middle of the NDR region. The second type is observed in the upper part of the double-plateau (figures 2(ii) and 2(iii)) with small amplitude (green). The plateau in this case is located at a current approximately three-quarters of the peak current. The second type of oscillation contains two Fourier components (figures 3 (ii-a) and (iii-a)),

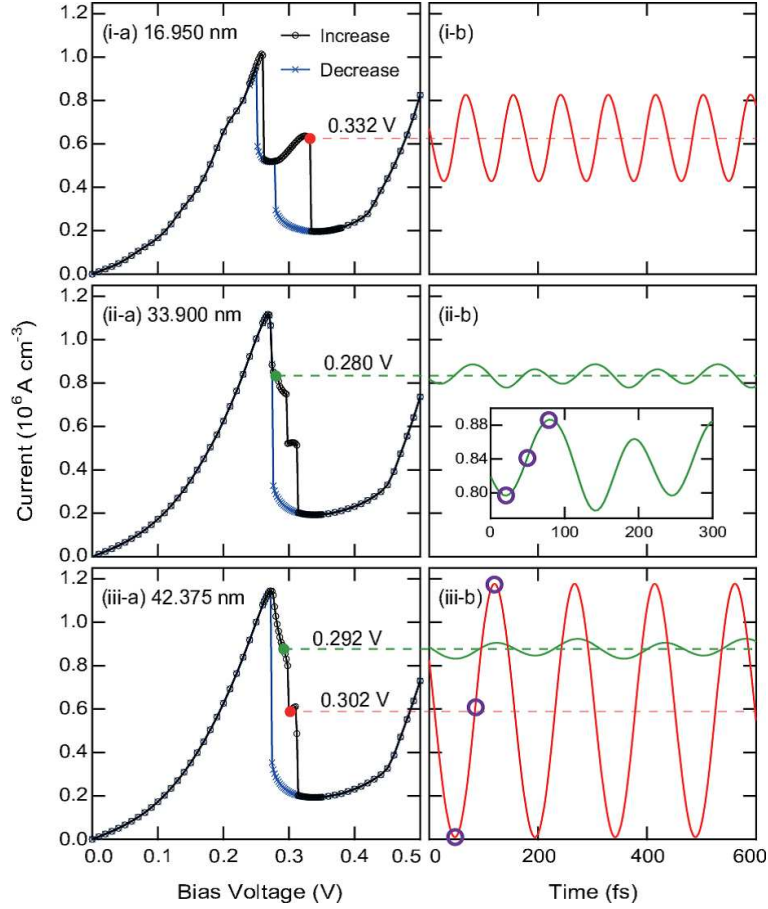


Figure 2. (a) The I-V characteristics for three sizes of the contact regions: (i) 16.950 nm; (ii) 33.900 nm; (iii) 42.375 nm. The black curve with circles represents the case in which the bias is increasing, and the blue curve with the $\times$ s represents the case in which the bias is decreasing. (b) Time evolution of the current for the value of the bias voltage at which current oscillation occurs. The red curves represent the current oscillation with large amplitude, and the green curves represent the current oscillation with small amplitude. The inset in (ii-b) contains a close-up view of one portion of the current. The snapshots of the Wigner distribution at the time points marked with purple circles are presented in figures 4 and 5.

whereas the first type contains just a single component (figures 3 (i-a) and (iii'-a)). We find that as the size of the contact regions increases, the frequency of each peak decreases.

As mentioned by Klusdahl *et al.* [60] and Zhao *et al.* [62], the quantum well formed on the emitter side of the effective potential plays an important role in the realization of hysteresis and plateau-like structure in the NDR region. The time averaged electron densities (black dashed curves) and the effective potentials (black solid curves) calculated from the Wigner distribution function in the case of increasing bias are plotted in figures 3 (i-b)-(iii'-b). For reference, in Appendix A, we present a graph corresponding to figure 3 (iii'-b) depicting the situation in the case of decreasing bias. A basin-like potential

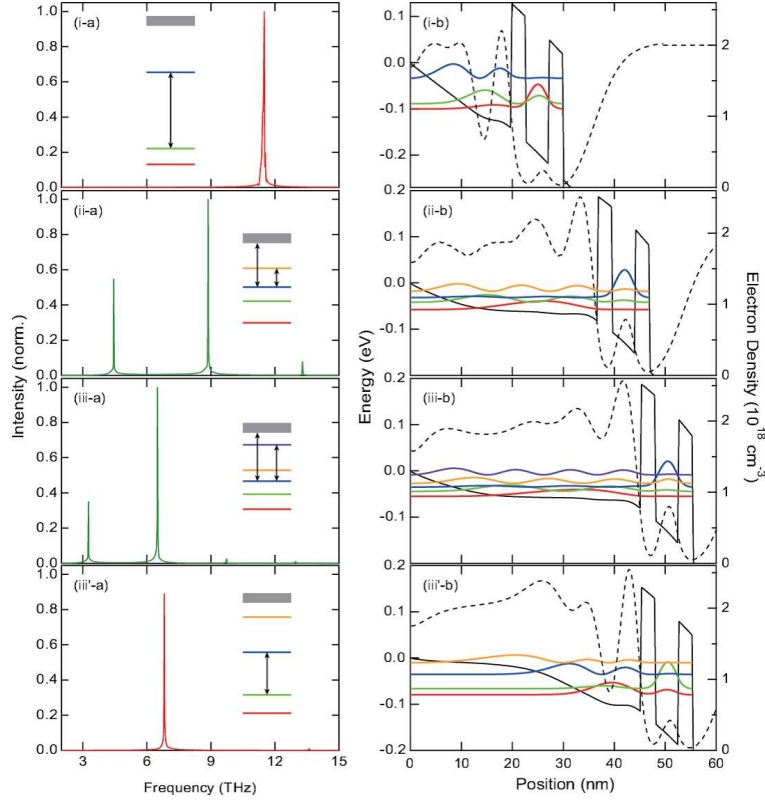


Figure 3. (a) The frequency distribution of the current oscillation that arises in the plateau region in the case of increasing bias. The size of contact region and the bias voltage are as follows: (i) 16.950 nm and 0.332 V (red curve in figure 2(i-b)); (ii) 33.900 nm and 0.280 V (green curve in figure 2(ii-b)); (iii) 42.375 nm and 0.292 V (green curve in figure 2(iii-b)); (iii') 42.375 nm and 0.302 V (red curve in figure 2(iii'-b)). The insets depict the corresponding transitions. The colored lines represent the eigenstates in the emitter basin given in the right graph, while the thick grey line represents the continuous energy band. (b) The time-averaged effective potential (black solid curve) and time averaged electron density (black dashed curve) for (i)-(iii'). The red, green, blue, orange, and purple curves represent the eigenstates in order of increasing eigenenergy calculated using the averaged effective potential without the heat bath.

on the emitter side (emitter basin) is observed in the case of increasing bias, while the emitter basin does not exist in the case of decreasing bias. In the case of increasing bias, when the bias exceeds the peak point of the I-V curve, the kinetic energy of the inflowing electron becomes larger than the eigenenergy of the resonant tunneling state. As a result, the reflection of the current from the emitter side of the barrier becomes large, and the electron distribution function becomes concentrated near the barrier, as depicted in figure 3 (i-b) - (iii'-b). When the electron density increases, the effective potential decreases. As a result, the emitter basin appears. When the emitter basin becomes sufficiently large, there appear resonant tunneling states between the emitter basin and the double-barrier well. In such a case, we find current oscillation and a plateau of the I-V curve in the NDR region. In the case of decreasing bias, however,

because there is no resonant tunneling state between the emitter and double-barrier well, the current is much smaller than in the case of the increasing bias. This difference causes the hysteresis behavior.

To elucidate this point more clearly, we solve the Schrödinger equation for the emitter basin and the double-barrier well to obtain approximate eigenstates and eigenenergies of an electron whose energy is lower than the continuous energy band on the emitter side. It should be noted that we employ the time-averaged potential for the purpose of the graph, but the effective potential and the corresponding eigenstates actually vary in time, because they depend on the electron distribution function, and it varies in time. Thus, for example, the identifications of the first (red) and second (green) eigenstates and the third (blue) and fourth (orange) eigenstates change in time, often becoming degenerate and interchanging. In addition, we ignore the continuous band on the collector side and the influence of the heat bath when calculating the eigenstates and eigenenergies. For this reason, the calculated eigenenergies are not precise, but we find that they are sufficient for determining the cause of the current oscillation, because each resonant frequency is rather isolated when estimating the oscillation frequency.

We find that each oscillation peak in both the large and small oscillation cases can be attributed to transitions between eigenstates in the emitter basin, as depicted in the insets of figures 3(i-a)-3(iii'-a). As shown in figures 3 (i-b) and 3 (iii'-b), the first eigenstate is the tunneling state in the large oscillation case, while the third eigenstate in figures 3 (ii-b) and (iii-b) is the tunneling state in the small oscillation case. When we compare the profiles of each eigenstate and the electron density distributions, we find that the tunneling state and the higher energy eigenstate close to the tunneling state are populated in both cases. Thus, we conclude that the current oscillation results from transitions between these two states, with the frequency of the oscillation determined by the frequency of these transitions. Because the structure of the emitter basin is stable with respect to change of the bias voltage, a plateau forms. As the size of the contact regions increases, the transition frequencies decrease, because the size of the emitter basin increases, while the depth of the basin does not change. This accounts for the peak shift seen in figures 3 (i-a) and 3 (iii'-a) and figures 3 (ii-a) and 3 (iii-a). Because the emitter basin becomes more stable with respect to change in the bias voltage as the contact regions becomes smaller, the plateau becomes large when we decrease the size of contact regions.

Both figures 2 (ii) and (iii) exhibit double plateau-like features in the NDR region, but we find current oscillation only in the upper plateau in the case of figure 2 (ii). This is because the dissipation in the large oscillation case of figure 2(ii) is not sufficiently strong to create significant population of the tunneling states in the case of a small basin, for which the resonant frequencies between the tunneling states and adjacent states are large. In our previous study [63], we considered the same condition as in figure 2 (iii), with a value of γ half as large ($= 12.1$ THz). In that case, however, there was only upper plateau oscillation. This is because the effective system-bath coupling strength, estimated as $\propto \zeta\gamma^2\omega_c/(\gamma^2 + \omega_c^2)$, where ω_c is the characteristic frequency of

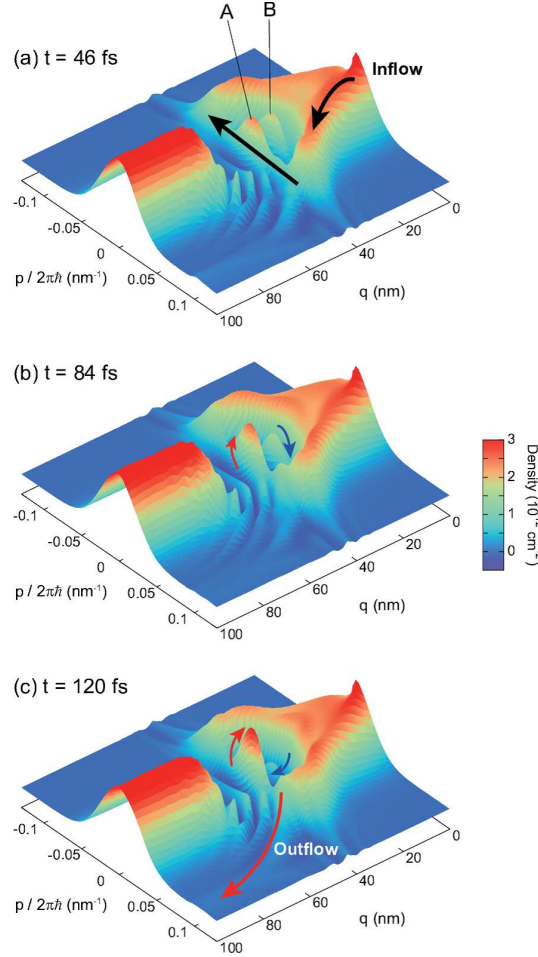


Figure 4. Current oscillation with a large amplitude observed in the lower part of the double-plateau structure at the times marked on the red curve in figure 2 (iii-b) depicted as snapshots of the Wigner distribution. (a) Current flows into the system from the emitter side of the boundary, and then it is scattered ($p_{in} \rightarrow -p_{in}$, where p_{in} is the momentum of the inflow current) by the emitter side of the barrier almost elastically. The scattered electron flows into peak B. (b) Peaks A and B become higher and lower in turn, exhibiting motion similar to that of pistons in a two-piston engine. (c) The current becomes large whenever peak A becomes large due to the tunneling.

the system [33], in the previous case is weaker than in the present case. Thus, in that case, the ground tunneling states are not populated from the conduction band through dissipation. Note, however, that if the system-bath coupling is too strong, dissipation suppresses the current oscillation, as explained in Appendix B.

One important aspect of the present methodology is that it allows elucidation of the dynamical behavior of the system through the time evolution of the Wigner distribution function. We have been able to characterize the patterns of the time evolution of the Wigner distribution for two types of current oscillations, with large and small oscillation amplitude. Here, we describe these two types in detail, using as one reference, the large oscillation case in figure 2 (iii-a) and the small oscillation case in figure 2 (ii-a). In

figure 4, we display snapshots of the Wigner distribution function for the case of large oscillation at the times marked on the red curve in figure 2 (iii-b). As illustrated in figures 3 (i-b) and 3 (iii'-b), the characteristic feature of this type of oscillation is the large electron density near the emitter side of the barrier, which is observed as a distinct peak separated from the conduction band (at $q = 42$ nm in figure 3 (iii'-b)). As a result of this feature, the effective potential possesses a deep emitter basin next to the barrier. The profiles of the eigenstates depicted in figure 3 (iii'-b) indicate that this peak consists of the first (red) to fourth (orange) eigenstates. We find that a small peak near the edge of the conduction state (at $q = 35$ nm in figure 3(iii'-b)), which arises from the third (blue) and fourth (orange) eigenstates in figure 3(iii'-b), also plays an important role in the current oscillation. In the Wigner distribution plotted in figure 4(a), these two peaks are denoted by A and B, respectively. In the situation depicted in figure 4 (a), the current flows into the system from the emitter side of the boundary, and then it is scattered by the emitter side of the barrier almost elastically, because the kinetic energy of the current electron is much higher than that of the tunneling state. The scattered current is trapped by the emitter basin and rotates clockwise around the peaks A and B, but, due to dissipation, some of it flows into peak B while losing energy. In the eigenstate representation given in figure 3(iii'-b), this behavior corresponds to population transfer from the fourth (orange) to the third (blue) eigenstate. In figure 4 (b), when the third (blue) state decays further to the first (red) and second (green) tunneling states, the height of A increases. As a result, peak A becomes higher, while peak B becomes lower. In figure 4(c), because peak A is related to the tunneling state, the outflow current becomes larger whenever peak A becomes higher. Throughout this process, the peaks A and B become higher and lower by turns, in a manner reminiscent of the piston in a two-piston engine. As a result of this motion, the current exhibits oscillation. This behavior is typical for this large oscillation case. Because there is no current in the case of Fig. 4 (a), the oscillation amplitude is large compared to that in the small oscillation case. If the dissipation is too strong, however, the piston-like motion is suppressed, and there is only steady current, as described in Appendix B.

In figure 5, we display snapshots of the Wigner distribution for the case of small oscillation at the times marked in figure 2 (ii). In figure 5 (a), while current flows into the system from the emitter side of the boundary, that part of it with energy larger than that of the tunneling state is scattered by the emitter side of the barrier. The remaining current, i.e., that whose energy is closer to the energy of the tunneling state, flows to the collector side in the form of steady current, through tunneling. In figure 5 (b), it is seen how the scattered electron moves back and forth in the emitter basin, while losing energy due to dissipation. As a result, the electron flows into peak C, exhibiting tornado-like motion. Figure 5 (c) depicts shaking motion of the effective potential that periodically accelerates the electron distribution in peak C to the tunneling state. Through this effect, current flows to the collector side through the barrier. Due to synchronization with this shaking motion, the current is enhanced periodically. This tornado-like motion is typical for the small oscillation case. Because there is a large contribution from steady

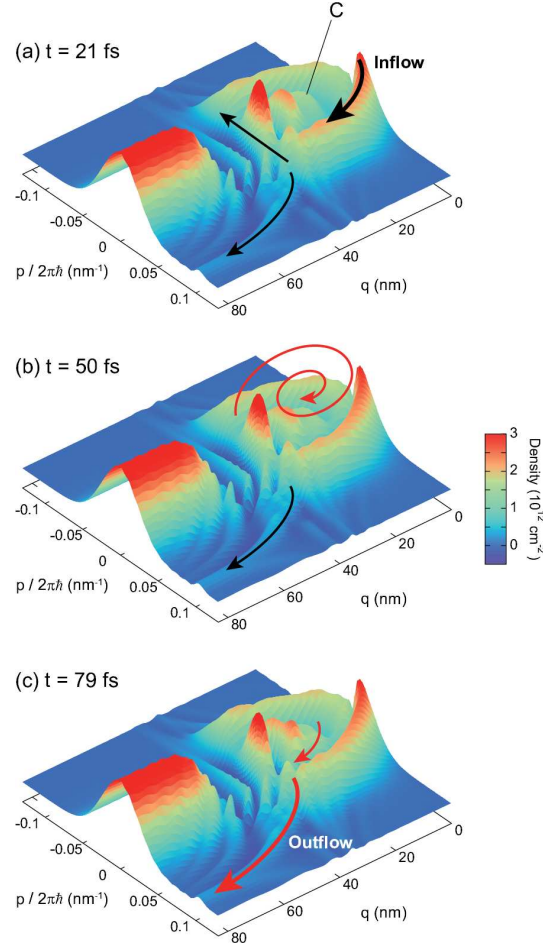


Figure 5. Current oscillation with small amplitude observed in the upper part of the double-plateau structure at the times marked on the green curve in figure 2 (ii) depicted as snapshots of the Wigner distribution. (a) Current flows into the system from the emitter side of the boundary. Then, a part of the current is scattered ($p_{in} \rightarrow -p_{in}$, where p_{in} is the momentum of the inflow current) by the emitter side of the barrier. The other part of the current flows to the collector side in the form of steady current through tunneling. (b) The scattered electron flows in a tornado-like manner to peak C in the emitter basin due to dissipation. (c) The shaking motion of the effective potential periodically accelerates the component at C to the tunneling state, and the current is thus enhanced.

current, the oscillation amplitude here is smaller than in the large oscillation case.

5. Conclusions

In summary, we investigated current oscillations in the plateau structures of the NDR region for three sizes of the contact regions with a model that includes damping, employing the Caldeira-Leggett Hamiltonian. We found two distinct types of current oscillations. The first type is observed in the single plateau and in the lower part of the double-plateau structure. It is characterized by a large oscillation amplitude and

a single Fourier component. The other type is observed in the upper part of double-plateau structure. It is characterized by a small oscillation amplitude and two Fourier components. An emitter basin that forms on the emitter side of the effective potential plays a key role in creating the current oscillation. Eigenstate analysis indicates that the first type is caused by transitions between the ground tunneling state and the adjacent excited state in the emitter basin, while the second type is caused by transitions between the intermediate tunneling state and higher states. Because the transition frequencies are large in the case of broad emitter basin, there is high frequency oscillation in the case of small contact regions for a fixed basin depth. In Wigner space, these two types of oscillation are characterized by the two types of motion: two-piston engine-like motion and tornado-like motion. Dissipation plays an important role in the realization of current oscillation. In order for the ground tunneling state to be populated in the case of large oscillation, there must be fairly strong dissipation, whose strength is determined by the system-bath coupling and the noise correlation time. If the dissipation is too strong, however, the current oscillation vanishes due to damped.

On the basis of the reduced hierarchy equations of motion (HEOM) approach, our investigation was carried out through highly accurate numerical calculations applied to a tunneling device system in a non-Markovian environment at finite temperature. While previous studies of this kind used the Boltzmann equation [60, 61, 62], we used the Caldeira-Leggett model. Although there is empirical evidence suggesting that the Boltzmann equation can be used to treat quantum dissipative dynamics, it is not quantum mechanically rigorous, unlike the Caldeira-Leggett model. We thus believe that our approach is superior. Although the validity of the Caldeira-Leggett Hamiltonian in the description of electron motion is not yet well established, we believe that the present results provide insight into the role of quantum mechanical phenomena in the type of system studied here.

The present approach can be used to treat a strong system-bath coupling non-perturbatively. In addition, any time-dependent external field can be added while taking into account the system-bath quantum coherence through the hierarchy elements. Such features are ideal for studying SQUID rings [9, 10] and quantum ratchet systems [11, 12].

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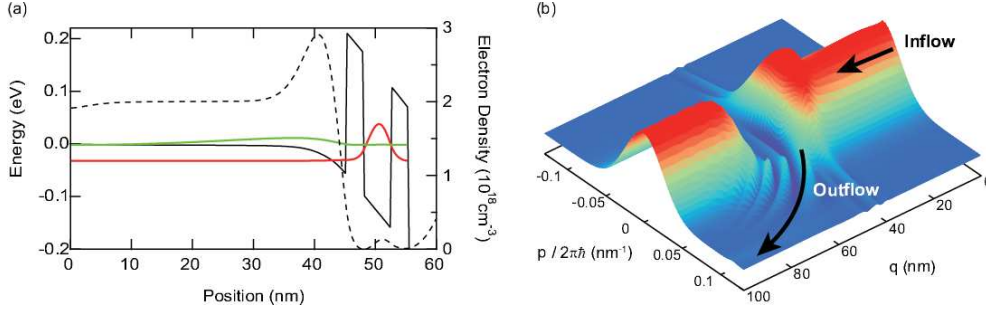


Figure A1. (a) The time-averaged effective potential (black solid curve) and time averaged electron density (black dashed curve) in the case of decreasing bias. Here, the width of the contact region is 42.375 nm, and the bias voltage is 0.302 V. In contrast to the cases considered in figures 3 (i-b)-(iii'-b), in the case considered here, the emitter basin is very small. The red and green curves represent the first and second eigenstates. (b) The steady-state Wigner distribution. The arrow indicates the direction of the steady current.

Appendix A. Effective potential and Wigner distribution in the case of decreasing bias

To understand the origin of hysteresis in the NDR region, we plot the effective potential, electron density and energy eigenstates of the emitter basin and double-barrier well in the case of decreasing bias in figure A1 (a). In this case, the emitter basin is so shallow that there is no tunneling state between the emitter basin and the double-barrier well. The existence of the peak near the barrier indicates that the second excited state is significantly populated. The current arises through the transition from the second excited state to the ground quantum state through dissipation. The Wigner distribution is plotted in figure A1 (b). Due to dissipation, the distribution is in a steady state. The peak near the barrier arises because the barrier impedes the flow. The electron density then leaks to the collector side without oscillation through tunneling in the form of steady current.

Appendix B. Strong coupling case

To see the effect of dissipation, we determined the I-V characteristics for the case of a stronger system-bath coupling, $\zeta = 120.8$ GHz ($\zeta^{-1} = 8.28$ ps). The values of the other parameters are the same as in figure 2. In contrast to the case considered in figure 2, in the present case current oscillation is not observed even in the plateau region. Also, the upper plateau does not exist. This is because the current oscillation decays quickly through the damping. Because the heat bath is strongly coupled to the system, the eigenstate picture of the electron system itself, as depicted in figure 3(b), is of questionable validity. As a result, the plateau is lost.

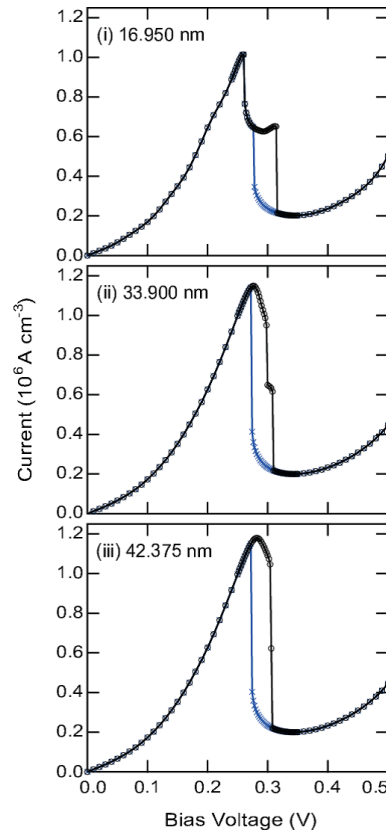


Figure B1. The I-V characteristics for the case of strong system-bath coupling, $\zeta = 120.8$ GHz ($\zeta^{-1} = 8.28$ ps). The values of the other parameters are the same as in figure 2. The black curve with the circles represents the case in which the bias is increasing, and the blue curve with the $\times$ s represents the case in which the bias is decreasing. Comparing this figure with figure 2(a), it is seen that the size of the NDR region is smaller and the plateau structure is less pronounced here than in the weak-coupling case. Current oscillation is not observed even in the plateau region.

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